

H5N2522LS

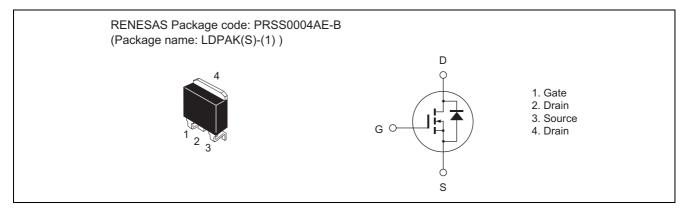
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1667-0100 Rev.1.00 Apr 23, 2008

Features

- Low on-resistance
- Low leakage current
- www.DataSheet4U.High speed switching
 - Built-in fast recovery diode

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	250	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	20	А
Drain peak current	I _{D (pulse)} Note1	60	А
Body-drain diode reverse drain current	I _{DR}	20	А
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	60	А
Avalanche current	I _{AP} ^{Note3}	20	А
Avalanche energy	E _{AR} ^{Note3}	25	mJ
Channel dissipation	Pch ^{Note2}	75	W
Channel to case thermal impedance	θch-c	1.67	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = $25^{\circ}C$

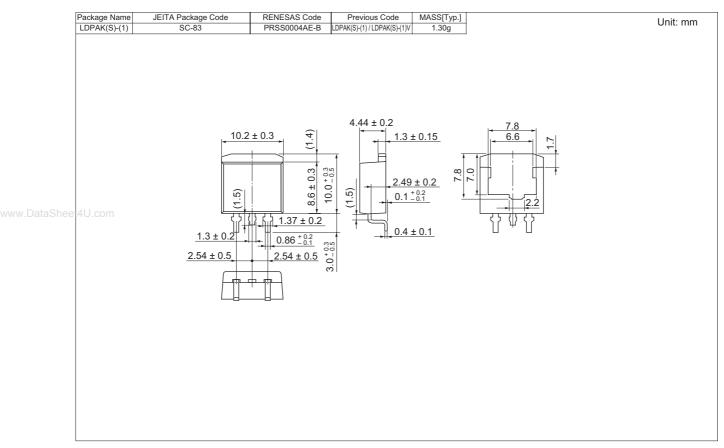
3. STch = 25° C, Tch $\leq 150^{\circ}$ C

Electrical Characteristics

							$(Ta = 25^{\circ}C)$
	Item	Symbol	Min	Тур	Max	Unit	Test conditions
	Drain to source breakdown voltage	V _{(BR)DSS}	250	_	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
	Zero gate voltage drain current	I _{DSS}	—		10	μΑ	$V_{DS} = 250 \text{ V}, \text{ V}_{GS} = 0$
	Gate to source leak current	I _{GSS}	—		±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
	Gate to source cutoff voltage	V _{GS(off)}	1.5		4.0	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
	Static drain to source on state resistance	R _{DS(on)}	_	0.14	0.18	Ω	$I_D = 10 \text{ A}, \text{ V}_{GS} = 10 \text{ V}^{\text{Note4}}$
	Input capacitance	Ciss	_	1300	_	pF	V _{DS} = 25 V
	Output capacitance	Coss	— 185 — pF V _{GS} = 0				
	Reverse transfer capacitance	Crss	—	62		рF	f = 1 MHz
www.DataShe	Turn-on delay time	t _{d(on)}	—	27		ns	I _D = 10 A
www.bataone	Rise time	tr	—	41		ns	$V_{GS} = 10 V$ $R_L = 12.5 \Omega$
	Turn-off delay time	t _{d(off)}	—	88		ns	
	Fall time	t _f	—	$-$ 16 — ns $Rg = 10 \Omega$			
	Total gate charge	Qg	_	47		nC	V _{DD} = 200 V
	Gate to source charge	Qgs	—	7		nC	$V_{GS} = 10 V$
	Gate to drain charge	Qgd	—	24.5		nC	I _D = 20 A
	Body-drain diode forward voltage	V _{DF}	_	0.99	1.54	V	$I_F = 20 \text{ A}, V_{GS} = 0^{Note4}$
	Body-drain diode reverse recovery time	t _{rr}	_	120		ns	$I_F = 20 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
H5N2522LSTL-E	1000 pcs	Taping

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